



DMS3015SSS

N-CHANNEL ENHANCEMENT MODE MOSFET WITH SCHOTTKY DIODE

Features

- DIOFET utilizes a unique patented process to monolithically integrate a MOSFET and a Schottky in a single die to deliver:
 - Low $R_{DS(ON)}\,$ minimizes conduction losses
 - Low V_{SD} reducing the losses due to body diode conduction
 - Low Q_{rr} lower Q_{rr} of the integrated Schottky reduces body diode switching losses
 - Low gate capacitance (Q_q/Q_{qs}) ratio reduces risk of shootthrough or cross conduction currents at high frequencies
 - Avalanche rugged I_{AR} and E_{AR} rated
- Lead Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

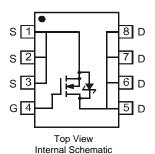
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.072 grams (approximate)





Top View



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 3) V _{GS} = 10V	Steady State	T _A = 25°C T _A = 85°C	I _D	11 6.6	А
Pulsed Drain Current (Note 4)			I _{DM}	80	Α
Avalanche Current (Notes 4 & 5)			I _{AR}	17	Α
Repetitive Avalanche Energy (Notes 4 & 5) L = 0.3mH			E _{AR}	43	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P _D	1.55	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 3)	$R_{\theta JA}$	81.3	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 Device mounted on 1in * 1in FR-4 PCB with 2oz. Copper. The value in any given application depends on the user's specific board design.
- 4. Repetitive rating, pulse width limited by junction temperature.
- 5. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep $T_J = 25^{\circ}C$

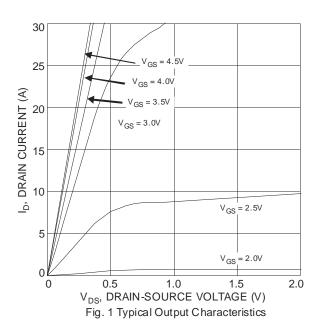


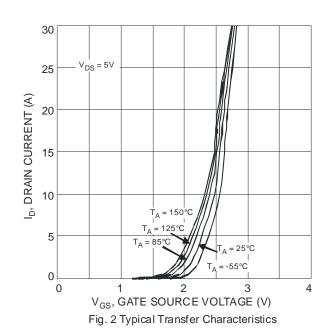
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	0.1	mA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.5	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	D	-	8.5 9.5	11.9 14.9	$\mathbf{m}\Omega$	$V_{GS} = 10V, I_D = 11A$	
Static Dialit-Source Off-Resistance	R _{DS (ON)}	-				$V_{GS} = 4.5V, I_D = 8.8A$	
Forward Transfer Admittance	Y _{fs}	-	18	-	S	$V_{DS} = 5V, I_{D} = 10A$	
Diode Forward Voltage	V_{SD}	-	0.45	0.55	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	-	1276	-	pF	151/1/ 01/	
Output Capacitance	Coss	-	160	-	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	136	-	pF	1 = 1.000112	
Gate Resistance	R_g	0.3	1.48	2.7	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	14.3	-	nC	$V_{DS} = 15V$, $V_{GS} = 4.5V$, $I_{D} = 8.8A$	
Total Gate Charge (V _{GS} = 10V)	Qq	-	30.6	-	nC	V _{DS} = 15V, V _{GS} = 10V, I _D = 8.8A	
Gate-Source Charge	Q_{gs}	-	3.4	-	nC		
Gate-Drain Charge	Q _{qd}	-	4.3	-	nC		
Turn-On Delay Time	t _{D(on)}	-	15.8	-	ns		
Turn-On Rise Time	t _r	-	27.8	-	ns	$V_{GS} = 4.5V, V_{DS} = 15V,$	
Turn-Off Delay Time	t _{D(off)}	-	29.7	-	ns	$R_G = 1.8\Omega, I_D = 8.8A$	
Turn-Off Fall Time	t _f	-	13.6	-	ns		

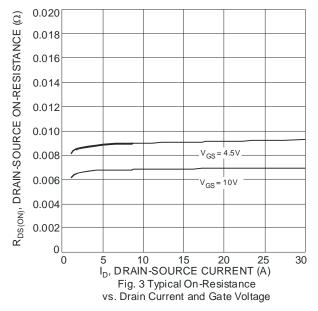
Notes:

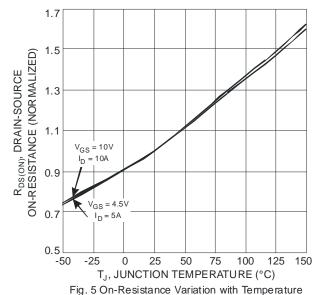
- 6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to production testing.











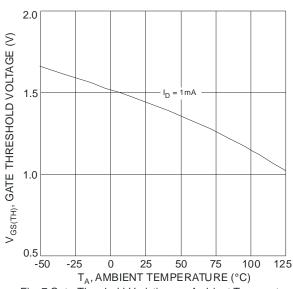
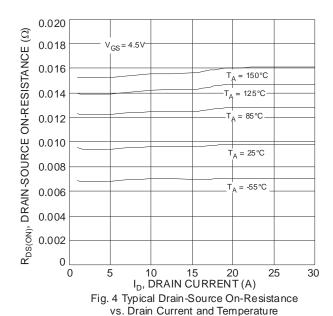
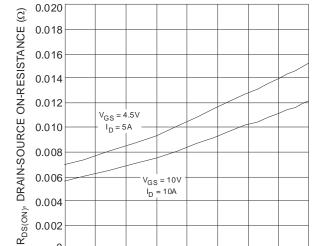


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





0.004

0.002 0

-50

-25

0

25

T_{.I}, JUNCTION TEMPERATURE (°C) Fig. 6 On-Resistance Variation with Temperature

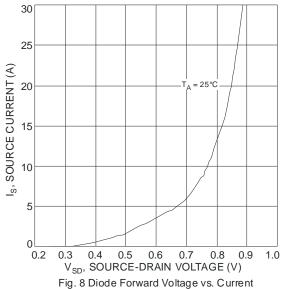
50

75

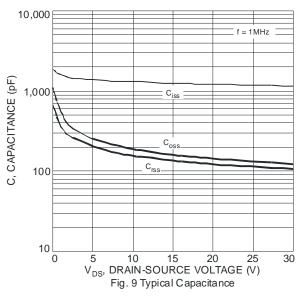
100

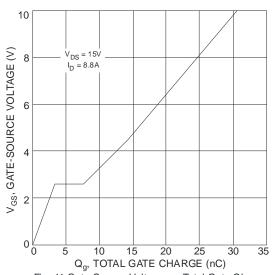
125

150









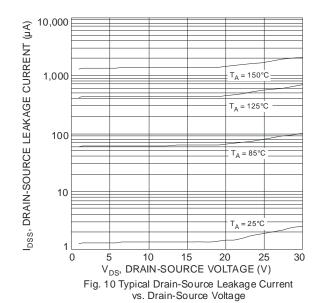
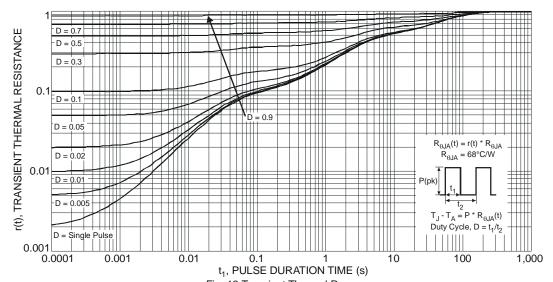


Fig. 11 Gate-Source Voltage vs. Total Gate Charge



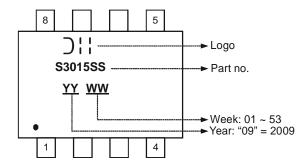


Ordering Information (Note 8)

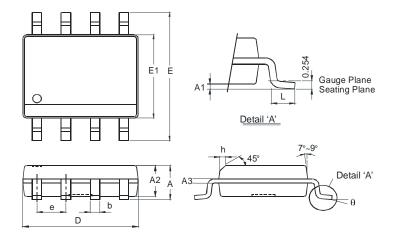
Part Number	Case	Packaging
DMS3015SSS-13	SO-8	2500 / Tape & Reel

Notes: 8. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

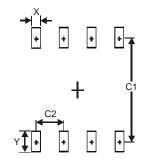


Package Outline Dimensions



SO-8				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	e 1.27 Typ			
h	-	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Υ	1.55
C1	5.4
C2	1.27



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